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EuMIC01: Millimeter-Wave GaN Devices and MMICs and Thermal Reliability Considerations

Chair: Dimitris Pavlidis, Boston University, USA

Co-Chair: Didier Floriot, United Monolithic Semiconductors, France

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¹United Monolithic Semiconductors, France; ²United Monolithic Semiconductors, Germany
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¹IEMN (UMR 8520), France; ²EpiGaN, Belgium
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¹LAAS, France; ²Université de Sherbrooke, Canada

EuMIC02: Millimeter-Wave Amplifiers and Detectors

Chair: Herbert Zirath, Chalmers University of Technology, Sweden

Co-Chair: Ingmar Kallfass, Universität Stuttgart, Germany

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¹Bergische Universität Wuppertal, Germany; ²GLOBALFOUNDRIES, Germany
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Chair: Frank van Vliet, TNO, The Netherlands

Co-Chair: Elisa Cipriani, Università di Roma "Tor Vergata", Italy

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¹Silicon Radar, Germany; ²IHP, Germany
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¹S3 Semiconductors, Ireland; ²S3 Semiconductors, Poland; ³S3 Semiconductors, Czech Republic

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¹SAE MICROELETTRONICA, Italy; ²STMicroelectronics, France

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Chair: Joaquín Portilla, UPV/EHU, Spain

Co-Chair: Mónica Fernández Barciela, Universidade de Vigo, Spain

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¹Universidade de Vigo, Spain; ²Cardiff University, UK

EuMIC06: Power Amplifier ICs

Chair: Frank van den Bogaart, TNO, The Netherlands

Co-Chair: Christophe Gaquiere, IEMN, France

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¹Indra Sistemas, Spain; ²Universidad Politécnica de Madrid, Spain
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Chair: Jonas Hansryd, Ericsson, Germany

Co-Chair: Yinggang Li, Ericsson, Germany

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¹FBH, Germany; ²IHP, Germany
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¹IHP, Germany; ²Michigan State University, USA
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¹Ericsson, Sweden; ²Chalmers University of Technology, Sweden
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¹Universität Stuttgart, Germany; ²Fraunhofer IAF, Germany

EuMIC08: MMIC Components

Chair: Asher Madjar, EuMA Founder Member, Israel

Co-Chair: Nuno Borges Carvalho, Instituto de Telecomunicações, Portugal

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¹ARELIS, France; ²IEMN (UMR 8520), France; ³IRCICA (USR 3380), France
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Chair: Alberto Santarelli, Università di Bologna, Italy

Co-Chair: Jean-Christophe Nallatamby, XLIM (UMR 7252), France

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¹University of Calgary, Canada; ²University of Sharjah, UAE; ³NRCC, Canada; ⁴UESTC, China
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Chair: Farid Medjdoub, IEMN (UMR 8520), France

Co-Chair: Rüdiger Quay, Fraunhofer IAF, Germany

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¹University of Toronto, Canada; ²GLOBALFOUNDRIES, Germany
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¹University of Southampton, UK; ²University of Sheffield, UK; ³University of Kent, UK
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Chair: Denis Barataud, XLIM (UMR 7252), France

Co-Chair: Carlos Crespo-Cadenas, Universidad de Sevilla, Spain

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¹Toshiba Research Europe, UK; ²University of Bristol, UK; ³Toshiba, Japan
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¹Waseda University, Japan; ²SRJ, Japan
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¹Politecnico di Torino, Italy; ²Cardiff University, UK
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Co-Chair: Franco Giannini, Università di Roma "Tor Vergata", Italy

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¹Waseda University, Japan; ²SRJ, Japan
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¹Goethe-Universität Frankfurt, Germany; ²FBH, Germany
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¹Technische Universität Berlin, Germany; ²GloMic, Germany

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Chair: Giovanni Ghione, Politecnico di Torino, Italy

Co-Chair: Teresa M. Martín-Guerrero, Universidad de Málaga, Spain

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¹Liverpool John Moores University, UK; ²Swansea University, UK; ³IEMN (UMR 8520), France; ⁴Université de Sherbrooke, Canada
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EuMC/EuMIC01: III-V Low Noise Amplifiers

Chair: Luisa de la Fuente, Universidad de Cantabria, Spain

Co-Chair: Julien Lintignat, XLIM (UMR 7252), France

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¹Middle East Technical University, Turkey; ²Analog Devices, USA
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¹FBH, Germany; ²Universität Duisburg-Essen, Germany
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EuMC/EuMIC02 : Doherty Power Amplifiers

Chair: Nathalie Delteil, IMS (UMR 5218), France

Co-Chair: Denis Barataud, XLIM (UMR 7252), France

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¹Politecnico di Torino, Italy; ²Cardiff University, UK; ³CityU, China

EuMC/EuMIC03 : Si-Based Amplifiers

Chair: Vadim Issakov, Infineon Technologies, Germany

Co-Chair: Beatriz Aja, Universidad de Cantabria, Spain

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EuMC/EuMIC04: EuMC/EuMIC Interactive Session

Chair: Jose A. Garcia, Universidad de Cantabria, Spain

Co-Chair: Luisa de la Fuente, Universidad de Cantabria, Spain

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¹United Monolithic Semiconductors, Germany; ²III-V Lab, France; ³United Monolithic Semiconductors, France; ⁴Universität Ulm, Germany

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¹Università dell'Aquila, Italy; ²Thales Alenia Space, Italy
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